
2SC5025

Silicon NPN Epitaxial

HITACHI

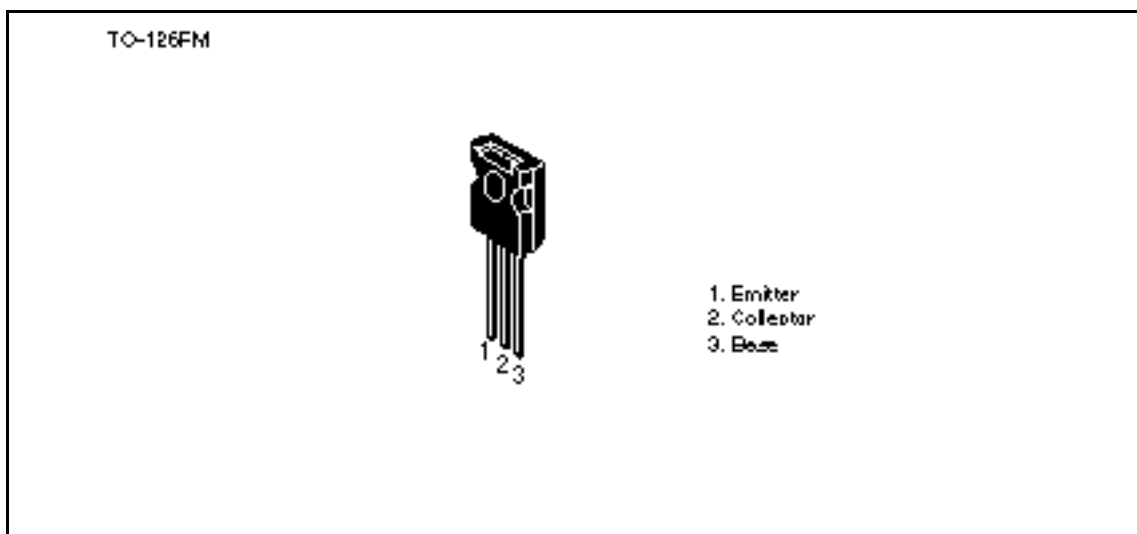
Application

High frequency amplifier

Features

- Excellent high frequency characteristics $f_T = 1.2$ GHz typ
- Low output capacitance $C_{ob} = 5.0$ pF typ

Outline



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Absolute Maximum Ratings (Ta = 25°C)

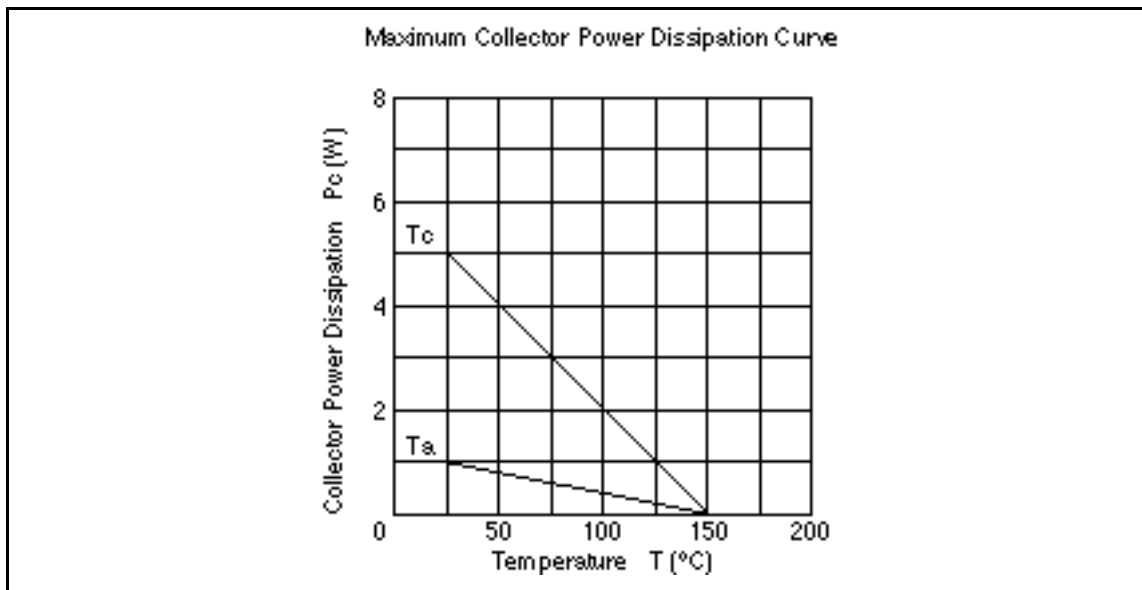
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3.5	V
Collector current	I_C	0.3	A
Collector peak current	$I_{C(peak)}$	0.5	A
Collector power dissipation	P_C	1	W
	P_C^{*1}	5	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 10\text{ mA}$, $R_{BE} =$
Collector cutoff current	I_{CBO}	—	—	1.0	mA	$V_{CB} = 25\text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	1.0	mA	$V_{EB} = 3\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	40	—	200		$V_{CE} = 5\text{ V}$, $I_C = 50\text{ mA}$
Base to emitter voltage	V_{BE}	—	—	1.2	V	$V_{CE} = 5\text{ V}$, $I_C = 300\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	2.0	V	$I_C = 300\text{ mA}$, $I_B = 60\text{ mA}$
Gain bandwidth product	f_T	—	1.2	—	GHz	$V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$
Collector output capacitance	C_{ob}	—	5.0	—	pF	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$
Input capacitance	C_{ib}	—	10	—	pF	$V_{EB} = 2\text{ V}$, $I_C = 0$, $f = 1\text{ MHz}$

See characteristic curves of 2SC3652.



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan
Tel Tokyo (03) 3270-2111
Fax (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA 94005-4835
U.S.A.
Tel 415-589-8300
Fax 415-589-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dannecker Straße 3
D-85622 Feldkirchen
München
Tel 089-9 24 80-0
Fax 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 6YA
United Kingdom
Tel 0628-885000
Fax 0628-778322

Hitachi Asia Pte. Ltd.
45 Collyer Quay #20-00
Hitachi Tower
Singapore 0404
Tel 535-2100
Fax 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 705, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel 27359218
Fax 27308074